

1

# Self-Biased PLL/DLL

ECG 721 – Memory Circuit Design (Spring 2017)

Dane Gentry

4/17/17

# Outline

- Jitter
- Self-Biased PLL/DLL
- Differential Buffer Delay
- Fig. 19.57
- Bias Generator
- Self-Biased DLL
  - Input/Output Delay Relationship
  - DLL Closed Loop Response
  - Bandwidth Tracking
  - Deriving  $\omega_N / \omega_{REF}$
  - Zero-Offset Charge Pump
- Self-Biased PLL
  - Input/Output Phase Relationship
  - PLL Closed Loop Response
  - Bandwidth Tracking
  - Deriving  $\omega_N / \omega_{REF}$
  - Feed-Forward Zero
  - **Complete** Self-Biased PLL
- References

- Jitter: the deviation from true periodicity of a presumably periodic signal, often in relation to a reference clock signal
- From CMOS: Circuit Design, Layout, and Simulation (pg. 591)
  - "Jitter, in the most general sense, for clock-recovery and synchronization circuits, can be defined as the amount of time the regenerated clock varies once the loop is locked."

• From CMOS: Circuit Design, Layout, and Simulation (pg. 591)



Figure 19.51 (a) Idealized view of clock and data without jitter and (b) with jitter.

• From CMOS: Circuit Design, Layout, and Simulation (pg. 589)



Figure 19.49 The PD (Hogge) portion of a self-correcting, clock-recovery circuit in lock.

• From CMOS: Circuit Design, Layout, and Simulation (pg. 589)



Figure 19.49 The PD (Hogge) portion of a self-correcting, clock-recovery circuit in lock.

• From CMOS: Circuit Design, Layout, and Simulation (pg. 589)



Figure 19.50 (a) Possible loop filter used in a self-correcting (Hogge) DPLL

- Desire high speed data transmission (need fast clock)
- High clock frequency (f) in Hertz, Hz → small clock period (T) in seconds, s
- Small jitter has more negative effect for small clock period
- Supply and substrate noise induced jitter

# Self-Biased PLL/DLL

Self-biased DLL/PLL designs achieve:

- Process technology and environmental variability independence
- Fixed damping factor (ζ)
- Fixed bandwidth to operating frequency ratio ( $\omega_N / \omega_{REF}$ )
  - bandwidth = loop bandwidth = natural frequency (radians/second, rad/s)  $\omega_N$
  - operating frequency (radians/second, rad/s)  $\omega_{\text{REF}}$
- $\omega_{\text{N}}$  that tracks  $\omega_{\text{REF}}$
- Broad  $\omega_{\text{REF}}$  range
- Low input tracking jitter / minimized supply and substrate noise induced jitter
- $\zeta$  and  $\omega_N/\omega_{REF}$  determined solely by ratio of capacitances (cap's)
- No external biasing (i.e. bandgap bias ckt)

# **Differential Buffer Delay**



- Used in both PLL/DLL
- Contains source coupled pair w/ resistive load elements called symmetric loads
- Sym. loads consist of diode-connected PMOS in shunt w/ equally sized biased PMOS
- $V_{CTRL}$  (loop filter output) generates NMOS/PMOS bias voltages (V\_{BP}) and (V\_{BN}), respectively
  - Defines lower voltage swing limit of buffer O/P's ( $V_{o+}$  swings VDD to  $V_{CTRL}$ )

## **Differential Buffer Delay**



- $V_{BP}$  approximately equal to control I/P to the bias generator ( $V_{CTRL}$ )
- NMOS current source dynamically biased w/  $\rm V_{BN}$  to compensate for drain and substrate volt. Variations
  - Provides high static supply and substrate noise rejection
- Buffer delay changes w/  $V_{\rm CTRL}$  since effective resistance of the load elements changes w/  $V_{\rm CTRL}$

#### Differential Delay Element and Voltage-Controlled Resistor

• From CMOS: Circuit Design, Layout, and Simulation (pg. 596)



Figure 19.57 A differential delay element based on a voltage-controlled resistor. The bias circuit adjusts the value of the resistors used in the delay elements to sink the current sourced by the p-channel MOSFETs.

#### **Bias Generator**



- $V_{CTRL}$  (control I/P to bias generator) produces bias voltages  $V_{BN}$  and  $V_{BP}$
- Bias generator continuously adjusts buffer bias current (2I<sub>D</sub>) to provide correct lower swing limit (V<sub>CTRL</sub>) for buffer stages
- Establishes constant current that is independent of supply volt. by using differential amplifier and half-buffer replica
- Amplifier adjusts V<sub>BN</sub> so that O/P volt. of half-buffer replica is V<sub>CTRL</sub>, the lower swing limit
- If supply volt. changes, amplifier will adjust to keep the swing and thus the bias current constant

#### **Bias Generator**



- Bias generator also provides buffered version of V<sub>CTRL</sub> at V<sub>BP</sub> O/P using additional half-buffer replica, isolating V<sub>CTRL</sub> from potential capacitive coupling in buffer stages
- Compact layout since sym. load uses same size PMOS's
- Bias Initial circuit is self-bias reference aka start up circuit



- Neg. f/b in loop adjusts delay through VCDL by integrating phase error that results b/w the periodic reference I/P and the delay line O/P
- Once in lock, VCDL will delay reference I/P by fixed amount to form the O/P such that there is no detected phase error b/w the reference and the O/P
- VCDL delay must be a multiple of the reference I/P clock period

# Input/Output Delay Relationship

$$D_O(s) = (D_I(s) - D_O(s)) \cdot F_{\text{REF}} \cdot \frac{I_{CH}}{sC_1} \cdot K_{DL}$$

- O/P delay D<sub>o</sub>(s): delay b/w reference I/P and DLL O/P (established by VCDL)
- I/P delay  $D_1(s)$ : delay to which the phase comparator compares the O/P delay
  - Phase difference for which phase comparator and charge pump generate no error signal
- Reference frequency (Hertz, Hz) F<sub>REF</sub>
- Charge pump current (Amps, A) I<sub>CH</sub>
- Loop filter capacitor (Farads, F) C<sub>1</sub>
- VCDL gain (seconds/Volt, s/V) K<sub>DL</sub>

#### **DLL Closed Loop Response**

• DLL has a first-order closed loop response since loop filter integrates the phase error

$$\frac{D_O(s)}{D_I(s)} = \frac{1}{1 + s/\omega_N} \qquad \qquad \omega_N = I_{CH} \cdot K_{DL} \cdot F_{\text{REF}} \cdot \frac{1}{C_1}$$

- +  $\omega_{N}$  will track  $\omega_{REF}$  if  $I_{CH}$  and  $K_{DL}$  are constant
- However,  $I_{CH}$ ,  $K_{DL}$ , and  $C_1$  are process technology dependent and will cause  $\omega_N$  to vary around the design target

• Delay is nonlinear w/ respect to  $V_{CTRL}$  and changes proportionally to  $1/(V_{CTRL} - V_T)$  w/ slope  $K_{DL}$  proportional to  $1/(V_{CTRL} - V_T)^2$  or  $1/I_D$ 



Typical symmetric load buffer stage delay as a function of control voltage

• Setting  $I_{CH} = 2I_D$  eliminates  $K_{DL}$  dependence on  $1/I_D$  which allows  $\omega_N$  to track  $\omega_{REF}$  without constraining  $\omega_{REF}$  range

# Deriving $\omega_N / \omega_{REF}$

$$t = R_{\rm EFF} \cdot C_{\rm EFF} = \frac{1}{g_m} \cdot C_{\rm EFF}$$

- Buffer delay (seconds, s) t
- Effective Resistance of sym. load (Ohms,  $\Omega$ ) R<sub>EFF</sub>
- Transconductance (Siemens, S OR mho,  $\mho$ )  $g_m$
- Effective buffer O/P capacitance (Farads, F) C<sub>EFF</sub>



- Using a half-buffer replica, the bias generator sets the buffer bias current equal to the current through a sym. load w/ its O/P volt. at  $V_{\rm CTRL}$
- In this case, the two equally sized PMOSs are both biased at  $V_{\rm CTRL}$  and each source half of the buffer bias current

# Deriving $\omega_N / \omega_{REF}$

• Drain current for one of the two equally sized PMOSs biased at  $V_{CTRL}$ :

$$I_D = \frac{k}{2} \cdot (V_{\text{CTRL}} - V_T)^2$$

where k is the device transconductance of one of the PMOS's

• Taking derivative w/ respect to V<sub>CTRL</sub>:

$$g_m = k \cdot (V_{\text{CTRL}} - V_T) = \sqrt{2 \cdot k \cdot I_D}$$

$$Deriving \omega_{N} / \omega_{REF}$$

$$t = R_{EFF} \cdot C_{EFF} = \frac{1}{g_{m}} \cdot C_{EFF}$$

$$g_{m} = k \cdot (V_{CTRL} - V_{T}) = \sqrt{2 \cdot k \cdot I_{D}}$$

$$\Rightarrow t = \frac{C_{EFF}}{k \cdot (V_{CTRL} - V_{T})}$$

• Delay (D) for n stage VCDL:

$$D = n \cdot t = \frac{C_B}{2 \cdot k \cdot (V_{\text{CTRL}} - V_T)}$$

Total buffer output capacitance for all stages (Farads, F) –  $C_B = 2*n*C_{EFF}$ 

# Deriving $\omega_N / \omega_{REF}$

• Delay (D) for n stage VCDL:

$$D = n \cdot t = \frac{C_B}{2 \cdot k \cdot (V_{\text{CTRL}} - V_T)}$$

• Taking derivative with respect to V<sub>CTRL</sub>:

$$K_{DL} = \left| \frac{dD}{dV_{CTRL}} \right| = \frac{C_B}{2 \cdot k \cdot (V_{CTRL} - V_T)^2}$$
$$= \frac{C_B}{4 \cdot I_D}$$

• Gain inversely proportional to buffer bias current

$$K_{DL} = \frac{C_B}{4 \cdot I_D}$$
 Deriving  $\omega_N / \omega_{REF}$ 

• Let  $I_{CH}$  be set to some multiple x of the buffer bias current:  $I_{CH} = x \cdot (2 \cdot I_D)$ 

$$\Rightarrow \quad \frac{\omega_N}{\omega_{\text{REF}}} = \frac{1}{\omega_{\text{REF}}} \cdot I_{CH} \cdot K_{DL} \cdot F_{\text{REF}} \cdot \frac{1}{C_1} \\ = \frac{1}{2\pi} \cdot I_{CH} \cdot K_{DL} \cdot \frac{1}{C_1} \\ = \frac{1}{2\pi} \cdot x \cdot (2 \cdot I_D) \cdot \frac{C_B}{4 \cdot I_D} \cdot \frac{1}{C_1} \\ = \frac{x}{4\pi} \cdot \frac{C_B}{C_1}$$

24

# Deriving $\omega_N / \omega_{REF}$

$$\frac{\omega_N}{\omega_{\rm REF}} = \frac{x}{4\pi} \cdot \frac{C_B}{C_1}$$

- $\omega_N / \omega_{REF}$  is constant and completely determined by a ratio of capacitances ( $C_B / C_1$ ) that can be matched reasonably well in layout
- Dramatically reduces process technology sensitivity

#### Zero-Offset Charge Pump

- Zero static phase offset, charge pump must transfer no net charge to the loop filter for equal duration UP and DN pulses
  - Requires UP and DN currents be identical and independent of the charge pump output voltage
- In-phase inputs:
  - Charge pump will see both UP and DN asserted for an equal and short period of time



 If in-phase PFC inputs produce no UP or DN pulses, it will take some finite phase difference before a large enough pulse is produced to turn on the charge pump, i.e. dead zone



- If reference is early, difference b/w UP and DN pulses will be equal to I/P phase difference
- Self-biasing allows charge pump to have zero static phase offset when UP and DN are asserted for equal durations on every cycle w/ in-phase inputs
- By constructing charge pump from sym. load buffer stage, UP and DN currents for equal duration pulses completely cancel out and transfer no net charge to loop filter

#### Zero-Offset Charge Pump

- Composed of 2 NMOS source coupled pairs each w/ a separate current source and connected by current mirror made from sym. load elements
- W/ both UP and DN asserted, left source-coupled pair behaves like half-buffer replica and produces V<sub>CTRL</sub> at current mirror node
- PMOS in right source coupled pair will have V<sub>CTRL</sub> at its gate and drain which is connected to loop filter
- PMOS will then source exact same buffer bias current sunk by remainder of source coupled pair
- W/ no net charge transferred to loop filter, charge pump will have zero static phase offset



Offset-cancelled charge pump with sym. loads

- Current mirror constructed from sym. load elements
- Unselected source coupled pair outputs connected to sym. load elements to match the voltages at the other outputs





• Res. used for stability

# Input/Output Phase Relationship

 PLL has a second-order closed response b/c loop filter integrates the charge representing the phase error and the VCO integrates the O/P freq. to form the O/P phase

$$P_O(s) = \left(P_I(s) - \frac{P_O(s)}{N}\right) \cdot I_{CH} \cdot \left(R + \frac{1}{sC_1}\right) \cdot K_V \cdot \frac{1}{s}$$

- Output phase P<sub>o</sub>(s)
- Input phase P<sub>I</sub>(s)
- Charge pump current (Amps, A) I<sub>CH</sub>
- Loop filter resistor (Ohms,  $\Omega$ ) R
- Loop filter capacitor (Farads, F) C<sub>1</sub>
- VCO gain (Hertz/Volt, Hz/V)  $K_V$

#### PLL Closed Loop Response

$$\frac{P_O(s)}{P_I(s)} = \left(\frac{1}{N} + \frac{s}{I_{CH} \cdot (R + 1/(sC_1)) \cdot K_V}\right)^{-1}$$
$$= \frac{N \cdot (1 + s \cdot C_1 \cdot R)}{1 + s \cdot C_1 \cdot R + s^2/(I_{CH}/C_1 \cdot K_V/N)}$$

$$\frac{P_O(s)}{P_I(s)} = N \cdot \frac{1 + 2 \cdot \zeta \cdot (s/\omega_N)}{1 + 2 \cdot \zeta \cdot (s/\omega_N) + (s/\omega_N)^2}$$

$$\zeta = \frac{1}{2} \cdot \sqrt{\frac{1}{N} \cdot I_{CH} \cdot K_V \cdot R^2 \cdot C_1}$$

where

$$\omega_N = \frac{2 \cdot \zeta}{R \cdot C_1}$$

- $\zeta$  = 1: Critically damped
- $\zeta > 1$ : Overdamped

- $I_{CH}$ , R, and  $K_V$  are constant for typical PLL  $\rightarrow$  const.  $\zeta$  and  $\omega_N$
- Const.  $\omega_N$  can constrain wide  $\omega_{REF}$  range and low I/P tracking jitter
- Want  $\omega_{\text{N}}$  as close to  $\omega_{\text{REF}}$  as possible to minimize total phase error
  - However,  $\omega_{\text{N}}$  must be a decade below the lowest  $\omega_{\text{REF}}$  for stability
- Ideally,  $\zeta$  and  $\omega_{N}/\omega_{REF}$  const. for improved jitter performance and no limit on  $\omega_{REF}$  range

- To keep  $\zeta$  constant w/  $\omega_{REF}$ ,  $I_{CH}$  can be set equal to buffer bias current (21<sub>D</sub>) and R can be set to vary inversely proportionally to the square root of the buffer bias current (R ~  $1/\sqrt{2I_D}$ )
  - $\Rightarrow \zeta \text{ const.}$ , but  $\omega_N$  will be proportional to square root of buffer bias current ( $\omega_N \sim \sqrt{2I_D}$ )
- For tracking bandwidth, VCO operating freq. should have same dependency on buffer bias current as  $\omega_{\text{N}}$

• Sym. load buffer stages used to implement VCO to obtain a broad frequency range



Typical VCO frequency as a function of control voltage when implemented with symmetric load buffer stages

- Freq. proportional to  $V_{CTRL}$   $V_T$  or, equivalently, the square root of  $I_D$  ( $\sqrt{I_D}$ ) and slope const. slope
  - $\rightarrow$  K<sub>v</sub> const. and  $\omega_{\text{REF}}$  proportional to square root of buffer bias current ( $\sqrt{2I_D}$ )
- Both  $\omega_{\rm N}$  and  $\omega_{\rm REF}$  proportional to  $\sqrt{2I_D}$ 
  - $\Rightarrow \omega_N$  will track  $\omega_{REF}$

# Deriving $\omega_N / \omega_{REF}$

• Oscillation freq. (F) of n-stage VCO:  
• 
$$F \sim \sqrt{2I_D}$$
  $F = \frac{1}{2 \cdot n \cdot t} = \frac{k \cdot (V_{\text{CTRL}} - V_T)}{C_B} = \frac{\sqrt{2 \cdot k \cdot I_D}}{C_B}$ 

- Taking derivative w/ respect to  $V_{\text{CTRL}}$ :  $K_V = \left| \frac{dF}{dV_{\text{CTRL}}} \right| = \frac{k}{C_B}$ 
  - Independent of buffer bias current

• Let I<sub>CH</sub> be set to some multiple x of the buffer bias current: 
$$\ I_{CH} = x \cdot (2 \cdot I_D)$$

 Let diode-connected sym. load in bias generator that establishes loop filter resistance be y times larger than sym. loads used in buffer stages

$$R = \frac{y}{2 \cdot g_m} = \frac{y}{\sqrt{8 \cdot k \cdot I_D}}$$

35

# $Deriving \omega_{N} / \omega_{REF}$ $K_{V} = \left| \frac{dF}{dV_{CTRL}} \right| = \frac{k}{C_{B}} \qquad I_{CH} = x \cdot (2 \cdot I_{D}) \qquad R = \frac{y}{2 \cdot g_{m}} = \frac{y}{\sqrt{8 \cdot k \cdot I_{D}}}$ $\zeta = \frac{1}{2} \cdot \sqrt{\frac{1}{N} \cdot I_{CH} \cdot K_{V} \cdot R^{2} \cdot C_{1}} \qquad \qquad \frac{\omega_{N}}{\omega_{REF}} = \frac{1}{2\pi \cdot F_{REF}} \cdot \frac{2 \cdot \zeta}{R \cdot C_{1}}$ $= \frac{1}{2} \cdot \sqrt{\frac{1}{N} \cdot x \cdot (2 \cdot I_{D}) \cdot \frac{k}{C_{B}} \cdot \frac{y^{2}}{8 \cdot k \cdot I_{D}} \cdot C_{1}} \qquad \qquad = \frac{1}{2\pi} \cdot \frac{N \cdot C_{B}}{\sqrt{2 \cdot k \cdot I_{D}}} \cdot \frac{y}{4} \cdot \sqrt{\frac{x}{N}} \cdot \sqrt{\frac{C_{1}}{C_{B}}}$ $= \frac{y}{4} \cdot \sqrt{\frac{x}{N}} \cdot \sqrt{\frac{C_{1}}{C_{B}}}.$ $= \frac{x \cdot N}{2\pi} \cdot \sqrt{\frac{C_{B}}{C_{1}}}.$

•  $\zeta$  and  $\omega_N/\omega_{REF}$  are both equal to a const. times square root of the ratio of two capacitances =  $x^*\sqrt{C_1/C_B}$ 

•  $\omega_N$  will track  $\omega_{REF}$  and, therefore, sets no constraint on the operating frequency range

#### Feed-Forward Zero

Form res. (R) to vary proportionally to 1/√2I<sub>D</sub> from small-signal resistance 1/g<sub>m</sub> for diode-connected device
 → (g<sub>m</sub> ~ √2I<sub>D</sub>)



Loop filter transformation for integration of loop filter res.

- V<sub>CTRL</sub> typically sum of volt. drops across cap. and res.
- Volt. drops across cap. and res. generated separately
  - As long as same charge pump current is applied to each of them
- 2 volt. drops summed to form V<sub>CTRL</sub> by replicating volt. across cap. w/ volt. source placed in series w/ res.
- Bias generator can implement this volt. source and res. since it buffers V<sub>CTRL</sub> to form V<sub>BP</sub> with a finite O/P resistance



Complete self-biased PLL block diagram

- Res. formed by diode-connected sym. load or, equivalently, a diode-connected PMOS device as seen in Bias Generator
  - Resistance is equal to  $1/g_m$  or inversely proportional to  $\sqrt{2I_D}$
- Self-biased PLL completed by adding additional charge pump current to bias generator's O/P

#### References

- [1] Maneatis, John G., "Low-Jitter Process-Independent DLL and PLL Based On Self-Biased Techniques," in IEEE Journal of Solid-State Circutis, Vol.33, No.11, Nov 1996.
- [2] Maneatis, John G., "Precise Delay Generation Using Coupled Oscillators," in ProQuest Dissertations and Theses, 1994.
- [3] Baker, R. Jacob, "CMOS Circuit Design, Layout, and Simulation," 3rd ed., Wiley-IEEE Press, 2010.

# Questions???